Supplementary Information

## Viable post-electrode-engineering for the complete integrity of largevolume-change lithium-ion battery anodes

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Figure S1. Adsorption-desorption isotherm curves for the annealed Si and bare Si electrodes.



Figure S2. TGA result for GSi to measure the carbon content added by rGO coating.



Figure S3. Surface FE-SEM image for (a)/(b) Gsi and, (b)/(c) rGO seed layer coated on the GSi. Across the opaque view of the rGO seed layer, Si particles can be confirmed.



Figure S4. (a)-(c) Surface FE-SEM image for deposition of MGZO MO on the GSi without the rGO seed layer. (d) Surface of MGZO film that is successfully deposited on the GSi with rGO seed layer. The MGZO film cannot show two-dimensional growth on the surface without a seed layer. Island-type growth for MGZO did not successfully settle during the sputtering deposition. The growth site was not found, and it had an amorphous form and could not be grown as a film on the GSi surface. The rGO does not need any post-removal step and can be easily applied using a facile spin coating method, thus it is a suitable seed layer for the subsequent deposition of the MGZO metal oxide layers.



Figure S5. XPS carbon/Si ratio for the Si and GSi electrodes.



Figure S6. XPS spectra of Mg, Ga, Zn and O in the GSi-MGZO.



Figure S7. Raman shift ratio of carbon and Si in conductive carbon free-GSi depending on depth.



Figure S8. Three-dimensional Raman elemental depth profiling for GSi electrode.



Figure S9. Raman shifts ratio of carbon and Si in the GSi electrode depending on depth.



Figure S10. Schematic of energy diagram for MGZO with Si anode depicting the electron barrier.



Figure S11. (a) SEM and (b)-(d) BSE images of the GSi. BSE image enable comfirming the hazy Si particles in the rGO web by whitish image (See circles in Figure S 10b).



Figure S12. EDS elemental mapping results for the electrochemically aggregated Si-rGO bulk.



Figure S13. Surface FE-SEM image for GSi after 200 cycles.



Figure S14. TEM images for the cycled bare Si electrode.



Figure S15. EELS spectra and STEM images for the fully-lithiated GSi-MGZO electrode. The measurement was conducted depending on the beam positions on the MGZO layer.



Figure S16. CV curves for the GSi-MGZO electrode according to the scan rate.



Figure S17. Galvanostatic charge/discharge curves for GSi-MGZO according to the current density.



Figure S18. Capacity retention rate (vs  $0.2 \text{ A g}^{-1}$ ) for the Si and the GSi-MGZO electrodes as a function of the current density. At a high current density up to 4 A g<sup>-1</sup>, the GSi-MGZO electrode shows an excellent capacity retention. At a current density of up to 2 A g<sup>-1</sup>, the capacity retention is more than 70%. However, in the case of the Si electrode, the capacity retention rate rapidly decreases to 4% at 4 A g<sup>-1</sup>, and there is an unfavorable capacity retention of 18% at a current density of 2 A g<sup>-1</sup>. The GSi-MGZO electrode exhibits a similar capacity even at 1 A g<sup>-1</sup> after testing at a current density of 4 A g<sup>-1</sup>, whereas the Si electrode exhibits a decreased capacity at 1 A g<sup>-1</sup> after the test at a high density of 4 A g<sup>-1</sup>.



Measured thickness: ~4.93 µm

Area: 0.785 cm<sup>2</sup>  
Thickness: 4.9 µm  
Mass: 0.43 mg  
Volumetric capacity = 
$$\frac{Specific \ capacity \ (mAh \ g^{-1}) \times Mass \ (g)}{Area \ (cm^2) \times Thickness \ (cm)}$$

Figure S19. Information related to volumetric capacity for GSi-MGZO.



Figure S20. (a) Initial galvanostatic charge/discharge curves for the Si/NMC811 full cell with variation in the current densities from 0.1 to 2 C. (b) Rate performance of the Si/NMC811 full cell with variation in the current densities from 0.1 to 2 C.

|  | Si     | Annealed Si |
|--|--------|-------------|
| Standard volume (cm <sup>3</sup> )                               | 34.163 | 34.163      |
| Dead volume (cm <sup>3</sup> )                                   | 38.678 | 38.727      |
| BET surface area(m <sup>2</sup> /g)                              | 6.47   | 7.76        |
| Total pore volume [p/p <sub>0</sub> =0.990] (cm <sup>3</sup> /g) | 0.170  | 0.211       |
| Mean pore diameter (nm)  | 105.16 | 109.02      |
| Maximum pore volume [cm <sup>3</sup> (STP)/g]                    | 1.486  | 1.782       |

Table S1. Details derived from BET plots for the annealed and bare Si electrodes.

Table S2. Representative literature data for volumetric capacity

| Materials                           | C-rate          | Volumetric capacity           | Reference |
|-------------------------------------|-----------------|-------------------------------|-----------|
| Carbon coated Si nanowires          | 0.2 C           | ~2500 mAh/cm <sup>3</sup>     | 1         |
| Shell coating nanoparticles         | 0.05 C          | 2041 mAh/cm <sup>3</sup>      | 2         |
| Carbon-garphene template            | 0.5 C           | 1807 mAh/cm <sup>3</sup>      | 3         |
| $SnO_2$ (2) Si nanospheres          | 0.075 C         | 1615 mAh/cm <sup>3</sup>      | 4         |
| Hierarchical Si@TiO <sub>2</sub> @C | 0.025 C         | 1174 mAh/cm <sup>3</sup>      | 5         |
| Porous Si microparticles            | 0.065 C         | 1075 mAh/cm <sup>3</sup>      | 6         |
| Carbon coated porous Si             | 0.05 C          | 1003 mAh/cm <sup>3</sup>      | 7         |
| GSi-MGZO                            | 0.025 C/ 0.25 C | 2766/2710 mAh/cm <sup>3</sup> | This work |

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